

MOSFET – Power, N-Channel, SUPERFET® III 800 V, 360 mΩ, 13 A

NTD360N80S3Z

Description

800 V SUPERFET III MOSFET is ON Semiconductor's high performance MOSFET family offering 800 V breakdown voltage.

New 800 V SUPERFET III MOSFET which is optimized for primary switch of flyback converter, enables lower switching losses and case temperature without sacrificing EMI performance thanks to its optimized design. In addition, internal Zener Diode significantly improves ESD capability.

This new family of 800 V SUPERFET III MOSFET enables to make more efficient, compact, cooler and more robust applications because of its remarkable performance in switching power applications such as Laptop adapter, Audio, Lighting, ATX power and industrial power supplies.

Features

- Typ. $R_{DS(on)}$ = 300 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 25.3 nC)
- Low Stored Energy in Output Capacitance (E_{oss} = 2.72 μJ @ 400 V)
- 100% Avalanche Tested
- ESD Improved Capability with Zener Diode
- RoHS Compliant

Applications

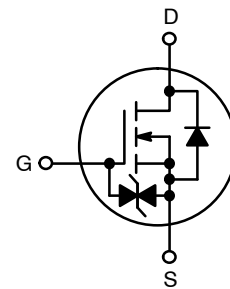
- Adapters / Chargers
- LED Lighting
- AUX Power
- Audio
- Industrial Power



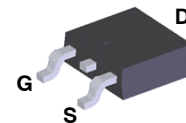
ON Semiconductor®

www.onsemi.com

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
800 V	360 mΩ	13 A



POWER MOSFET



D-PAK
TO-252
CASE 369AS

MARKING DIAGRAM



&Z = Assembly Plant Code
 &3 = Data Code (Year & Week)
 &K = Lot
 NTD360N80S3Z = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NTD360N80S3Z

ABSOLUTE MAXIMUM RATINGS (T_J = 25°C, unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{DSS}	Drain-to-Source Voltage	800	V
V _{GS}	Gate-to-Source Voltage	DC	±20
		AC (f > 1 Hz)	±30
I _D	Drain Current	Continuous (T _C = 25°C)	13
		Continuous (T _C = 100°C)	8.2
I _{DM}	Drain Current	Pulsed (Note 1)	32.5
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	40	mJ
I _{AS}	Avalanche Current (Note 2)	2.0	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	0.96	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 3)	10	
P _D	Power Dissipation	(T _C = 25°C)	96
		Derate Above 25°C	0.768
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from Case for 10 seconds)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I_{AS} = 2.0 A, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 3.25 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.

THERMAL RESISTANCE RATINGS

Symbol	Parameter	Value	Unit
R _{θJC}	Junction-to-Case - Steady State	1.3	°C/W
R _{θJA}	Junction-to-Ambient - Steady State	62.5	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Reel Size	Tape Width	Quantity
NTD360N80S3Z	NTD360N80S3Z	TO-252	330 mm	16 mm	2500 Units

NTD360N80S3Z

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain-to-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 1 mA, T _J = 25°C	800			V
		V _{GS} = 0 V, I _D = 1 mA, T _J = 150°C	900			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 1 mA, Referenced to 25°C		1.1		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 800 V, V _{GS} = 0 V			1	μA
		V _{DS} = 640 V, T _C = 125°C		0.8		
I _{GSS}	Gate-to-Body Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V			1	μA

ON CHARACTERISTICS

V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 0.3 mA	2.2		3.8	V
R _{DS(on)}	Static Drain-to-Source On Resistance	V _{GS} = 10 V, I _D = 6.5 A		300	360	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 6.5 A		13.8		S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 400 V, V _{GS} = 0 V, f = 250 kHz		1143		pF
C _{oss}	Output Capacitance			18.1		pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V		236.4		pF
C _{oss(er.)}	Energy Related Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V		34		pF
Q _{g(tot)}	Total Gate Charge at 10 V	V _{DS} = 400 V, I _D = 6.5 A, V _{GS} = 10 V (Note 4)		25.3		nC
Q _{gs}	Gate-to-Source Gate Charge			5.3		nC
Q _{gd}	Gate-to-Drain "Miller" Charge			8.3		nC
ESR	Equivalent Series Resistance	f = 1 MHz		4		Ω

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn-On Delay Time	V _{DD} = 400 V, I _D = 6.5 A, V _{GS} = 10 V, R _g = 25 Ω (Note 4)		21.2		ns
t _r	Turn-On Rise Time			18.5		ns
t _{d(off)}	Turn-Off Delay Time			110		ns
t _f	Turn-Off Fall Time			17.7		ns

SOURCE-DRAIN DIODE CHARACTERISTICS

I _S	Maximum Continuous Source-to-Drain Diode Forward Current			13		A
I _{SM}	Maximum Pulsed Source-to-Drain Diode Forward Current			32.5		A
V _{SD}	Source-to-Drain Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 6.5 A		1.2		V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 3.25 A, dI _F /dt = 100 A/μs		370		ns
Q _{rr}	Reverse Recovery Charge			3.2		μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

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TYPICAL CHARACTERISTICS

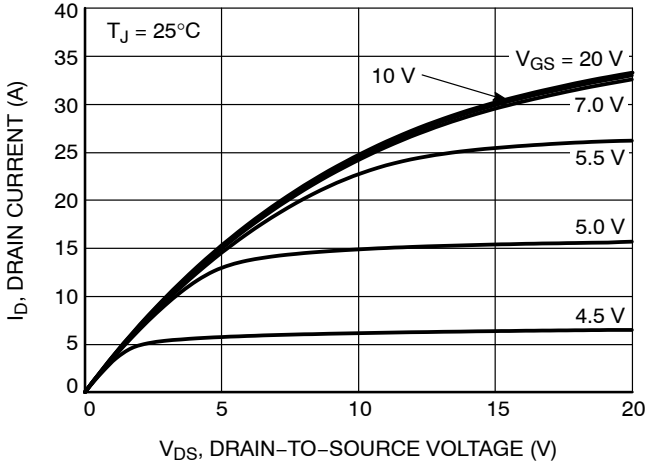


Figure 1. On-Region Characteristics

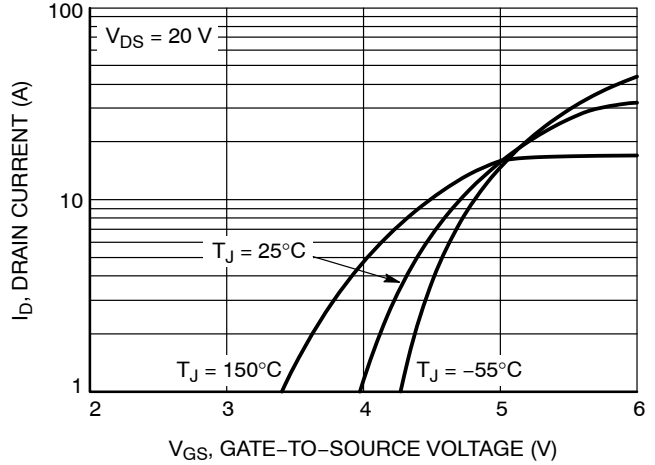


Figure 2. Transfer Characteristics

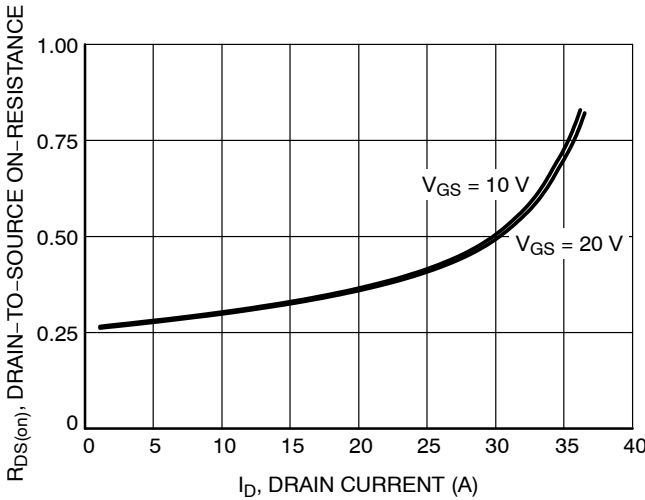


Figure 3. On Resistance vs. Drain Current

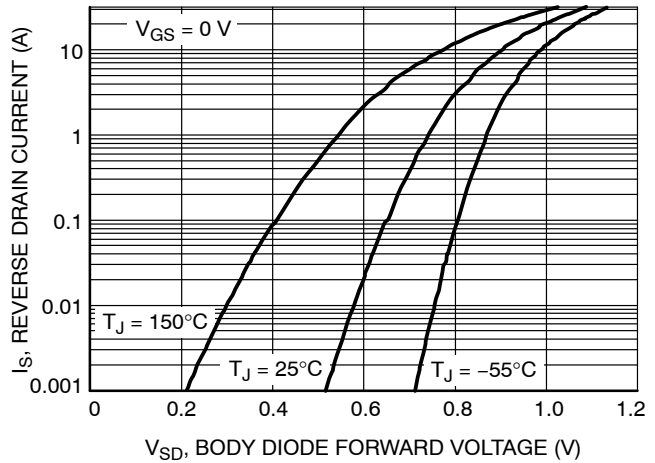


Figure 4. Diode Forward Voltage vs. Current

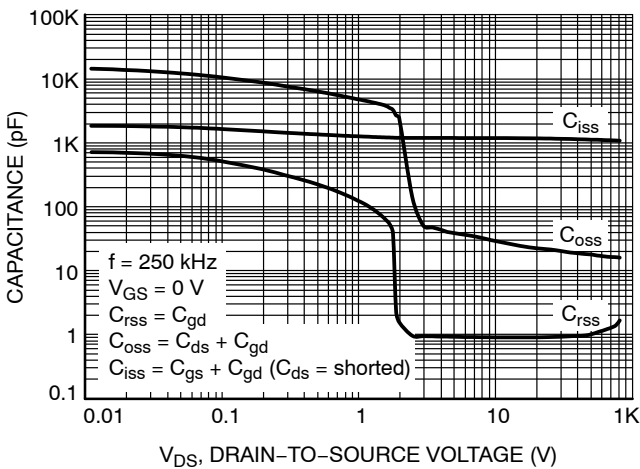


Figure 5. Capacitance Characteristics

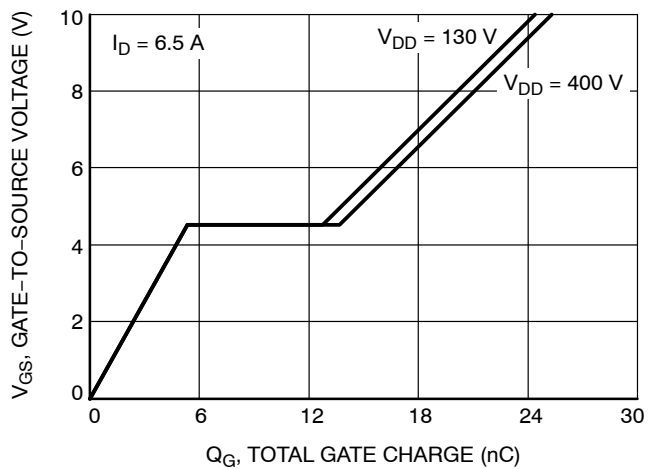


Figure 6. Gate Charge Characteristics

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TYPICAL CHARACTERISTICS

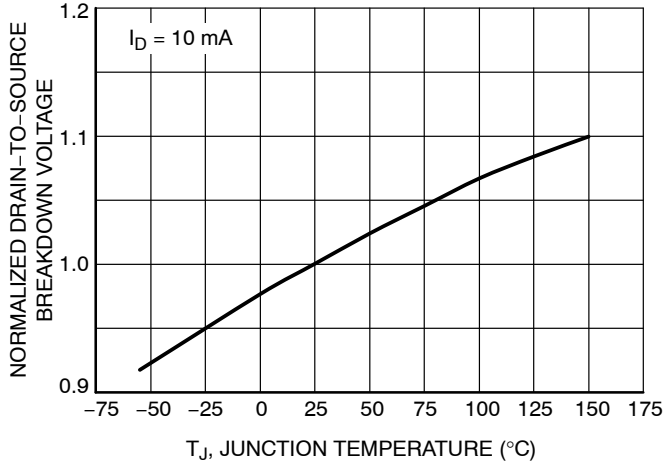


Figure 7. Normalized BV_{DSS} vs. Temperature

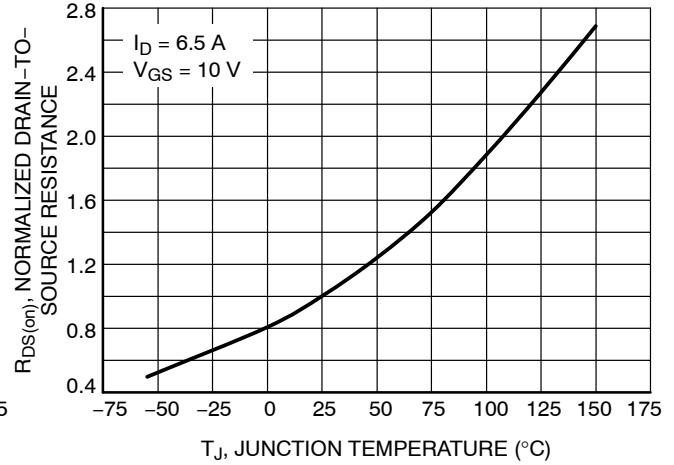


Figure 8. On-Resistance Variation vs. Temperature

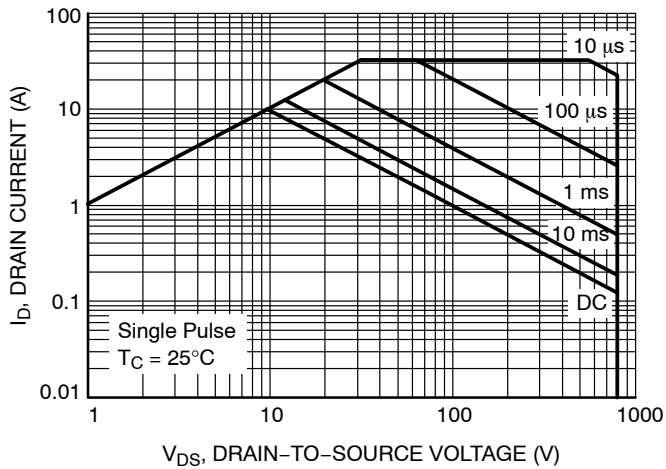


Figure 9. Safe Operating Area

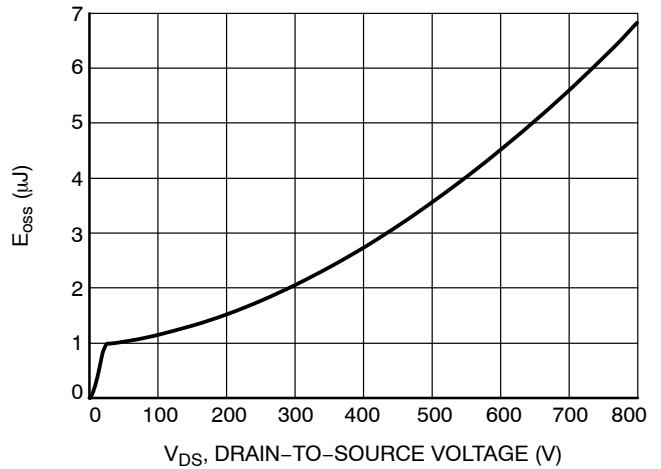


Figure 10. E_{oss} vs. Drain-to-Source Voltage

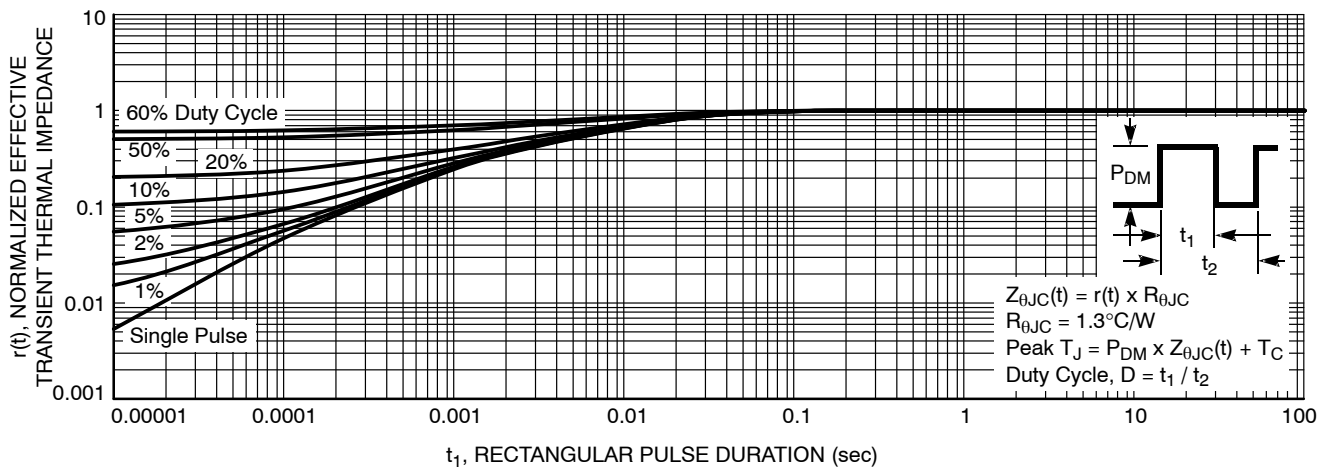


Figure 11. Transient Thermal Impedance

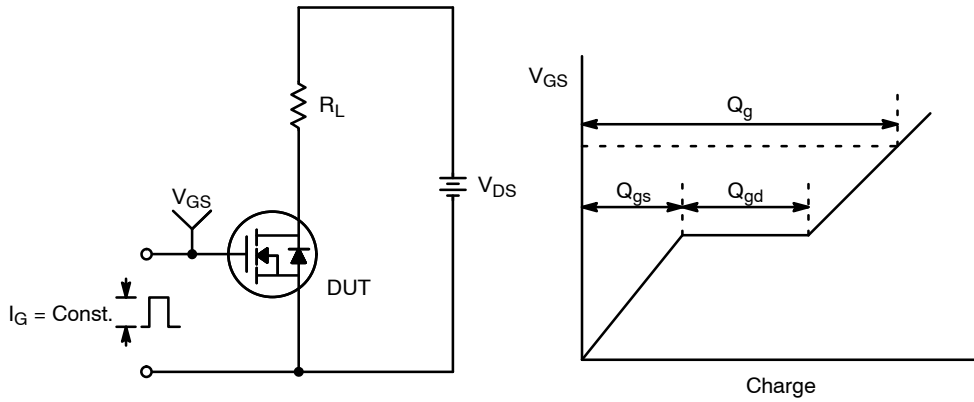


Figure 12. Gate Charge Test Circuit & Waveform

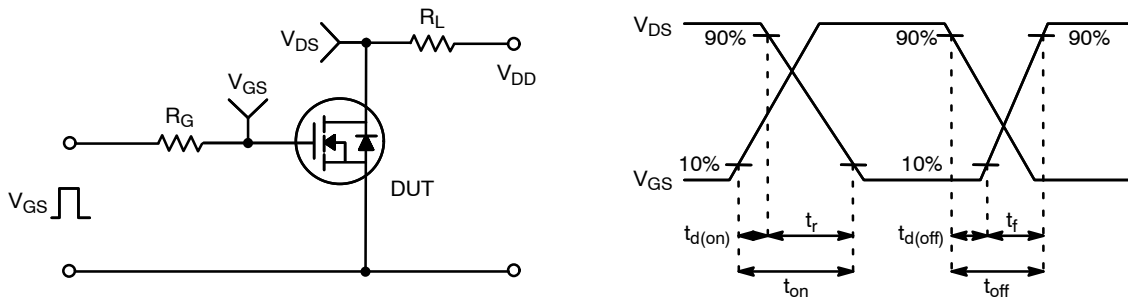


Figure 13. Resistive Switching Test Circuit & Waveforms

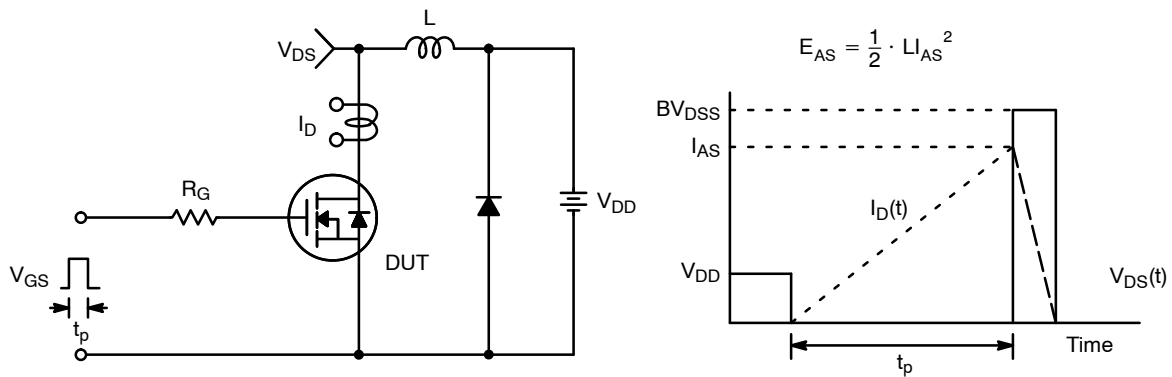


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

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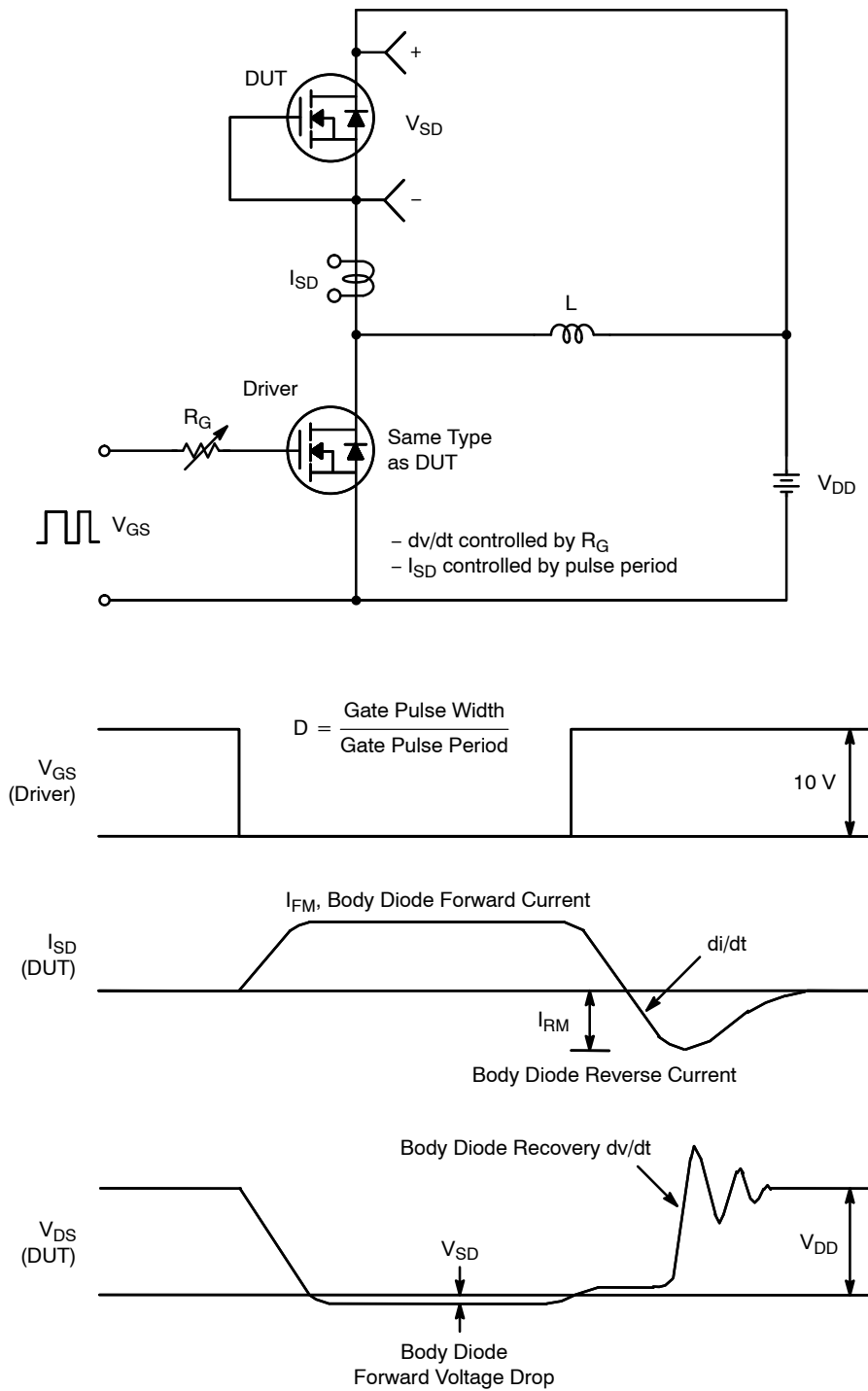
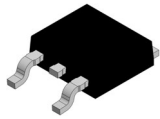


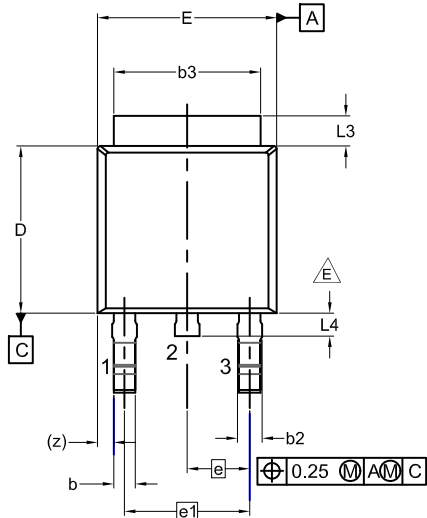
Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

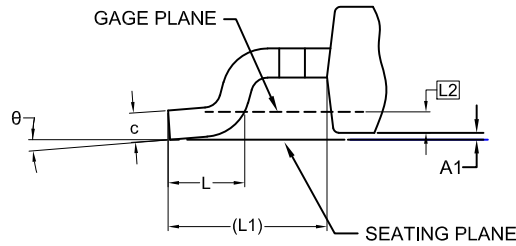


DPAK3 (TO-252 3 LD) CASE 369AS ISSUE A

DATE 28 SEP 2022

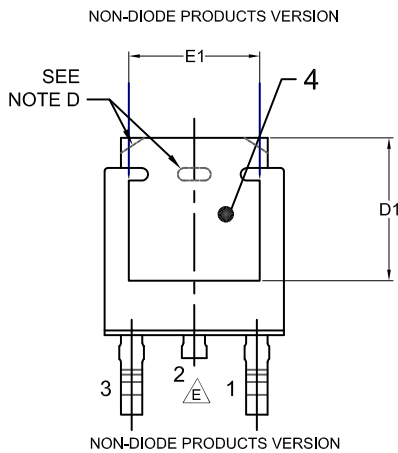


- NOTES: UNLESS OTHERWISE SPECIFIED
 A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
 D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
 E) FOR DIODE PRODUCTS, L4 IS 0.25 MM MAX.
 F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
 G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.



DETAIL A
(ROTATED -90°)
SCALE: 12X

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.18	2.29	2.39
A1	0.00	-	0.127
b	0.64	0.77	0.89
b2	0.76	0.95	1.14
b3	5.21	5.34	5.46
c	0.45	0.53	0.61
c2	0.45	0.52	0.58
D	5.97	6.10	6.22
D1	5.21	-	-
E	6.35	6.54	6.73
E1	4.32	-	-
e	2.286 BSC		
e1	4.572 BSC		
H	9.40	9.91	10.41
L	1.40	1.59	1.78
L1	2.90 REF		
L2	0.51 BSC		
L3	0.89	1.08	1.27
L4	-	-	1.02
θ	0°	--	10°

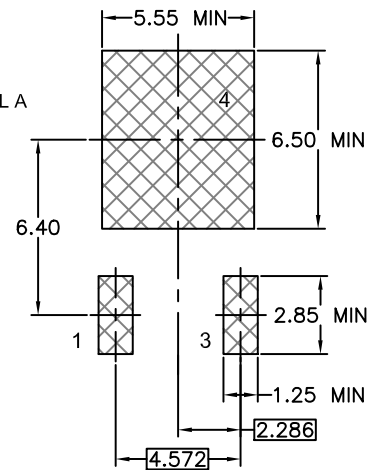


GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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